

Effects of Density of States Asymmetry on Boundary Resistance of Ferromagnetic-Nonferromagnetic Metal Interface

Pavel Krotkov^{1,2} and Maxim Dzero^{*1}

¹*National High Magnetic Field Laboratory, Florida State University, Tallahassee, Florida 32310, USA*

²*L.D. Landau Institute for Theoretical Physics, Russian Academy of Sciences, 2 Kosygina st., 117334 Moscow Russia*

Asymmetry of conduction of electrons in the spin majority and minority bands of a ferromagnetic metal is well known to produce spin accumulation at the boundary with a normal metal when a current is injected through the interface. However, little emphasis has been put on the density of states (DOS) asymmetry in diffusive ferromagnetic-nonferromagnetic multilayers. We found that if DOS and conduction asymmetry differ, the electric potential in a ferromagnet falls off to its bulk value exponentially on a scale of the spin diffusion length. Therefore the boundary contribution to resistance dramatically depends on whether the potential difference is measured close to the interface or farther than the spin diffusion length from it. This result is not altered by taking surface resistance or spin-flips on the intermetallic boundary into account. Explicit answers for common multilayered spin-valve structures are given.

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I. INTRODUCTION

The possibility to exploit electron spin to manipulate currents in electronic microdevices has generated wide interest in the rapidly expanding field of spin electronics [1, 2, 3]. Technically, the itinerant electron spin may be put to use if the spin-flip scattering, intermixing the spin-up and spin-down channels, occurs at a rate $\tau_{\uparrow\downarrow}^{-1}$ which is slow compared to the inverse mean free time τ^{-1} which characterizes the dissipative processes in charge of electrical resistivity. Separation of electrons in two channels is a key element of the physics of a central spintronics phenomenon of giant magneto-resistance (GMR) of metallic ferromagnetic-nonferromagnetic metal multilayers.

The two-channel description of diffusive electrical transport from a ferromagnetic (FM) to a nonferromagnetic metal was given in [4] and on a thermodynamic basis also in [5]. Due to the exchange splitting of the Fermi surface in a FM metal the Fermi energy corresponds to different parts of the band structure for spin-up and spin-down electrons, and therefore the two types of electrons have different densities of state $N_{\uparrow,\downarrow}$ and conductions $\sigma_{\uparrow,\downarrow}$. Because of the conduction asymmetry

$$\alpha = \frac{\sigma_{\uparrow} - \sigma_{\downarrow}}{\sigma_{\uparrow} + \sigma_{\downarrow}} \quad (1)$$

an electrical current passing from a FM to a nonferromagnetic metal is polarized and injects magnetization. This effect shows up as an additional contact resistance.

The size l_{sd} of the region of the spin accumulation is set by the equilibrium between spin injection through the interface and the spin-flipping processes in the bulk of the paramagnet. The spin diffusion length l_{sd} relates to the mean free path λ as $l_{sd}/\lambda \sim (\tau_{\uparrow\downarrow}/\tau)^{1/2}$. An analysis of

the two-channel model was given by Valet and Fert [6] on the basis of the Boltzmann transport equation in the limit $l_{sd} \gg \lambda$. They have also applied the model to the geometry of the GMR with current perpendicular to the plane (CPP-GMR). A significant advantage of their approach is the ability to describe measurable quantities in detail in terms of parameters of the theory, which allows to extract the latter from experiment [8, 9, 10].

The formulas in [6], however, have been derived in a flawed assumption that while the conductivities $\sigma_{\uparrow,\downarrow}$ of the majority and minority spins are different, the corresponding densities of states (DOS), $N_{\uparrow,\downarrow}$, are equal. But the difference in $N_{\uparrow,\downarrow}$ is essential as it leads to a jump of the electric potential on an intermetallic interface, which also was not observed in the later work [7]. Neglect of the difference in $N_{\uparrow,\downarrow}$ results in an incorrect variation of the electric potential with distance from an intermetallic interface, and changes, *inter alia*, the boundary contribution to resistance.

The aim of the present paper is to provide expressions for boundary resistances of common multilayered systems corrected to allow the measurements of potential drop to be performed at any distance from interfaces, not necessarily $\gg l_{sd}$. Correlative results for an array of domain walls have been obtained in [11]. In Sec. II a review of the two-channel diffusive transport theory is given, whereas in Sec. III we demonstrate our results for a single ferromagnetic-nonferromagnetic interface and for typical spin-valve structures. Sec. IV summarizes the findings and provides a brief discussion. Finally, an appendix with details of our approach to calculation is presented at the end of the paper.

II. BASIC EQUATIONS

Starting from the Boltzmann equation, Valet and Fert [6] showed that in the limit $l_{sd} \gg \lambda$ one can describe transport in the system introducing electrochemical po-

^{*}Present address: U.S. Department of Energy Ames Laboratory, Ames, IA 50011. E-mail: dzero@ameslab.gov.

tentials μ_ρ for the two spin channels $\rho = \uparrow, \downarrow$ as sums of chemical potentials (accounting for the kinetic energy of electrons) and the potential energy. For small deviations from equilibrium the chemical potential is given by the non-equilibrium electron density n_ρ divided by the density of states N_ρ on the Fermi surface:

$$\mu_\rho = n_\rho / N_\rho - eU. \quad (2)$$

Here $-e$ is the electron charge, U is the electric potential, and the condition $n_\uparrow = -n_\downarrow$ is fulfilled owing to electroneutrality.

We now briefly review the equations of two-channel diffusive transport to establish notations. Electron current $\mathbf{j}_\rho$ in the channel ρ is a sum of a diffusion component and a contribution from the electron drift under the influence of an electric field $\mathbf{E} = -\partial U$:

$$\mathbf{j}_\rho = -(-e)D_\rho \partial n_\rho + \sigma_\rho \mathbf{E} = \sigma_\rho \partial \mu_\rho / e, \quad (3)$$

where we used the Einstein relation $\sigma_\rho = e^2 N_\rho D_\rho$ between the conductivity σ_ρ and the diffusion constant D_ρ . In the bulk the excess electron density $n_\uparrow$ is zero, the electrochemical potentials for the two channels are equal: $\mu_\uparrow = \mu_\downarrow$, and the current polarization is α (1). Relaxation of non-equilibrium polarization of current near a boundary between two materials due to spin-flip processes is described by the continuity equations

$$\partial \mathbf{j}_\rho = en_\rho / \tau_{\uparrow\downarrow}. \quad (4)$$

It is convenient to introduce the divergence $\mu_s \equiv \mu_\uparrow - \mu_\downarrow$ between the two electrochemical potentials. It is non-zero only in the presence of spin accumulation: from (2) one finds that it is related to $n_\uparrow$ via

$$\mu_s = n_\uparrow (N_\uparrow^{-1} + N_\downarrow^{-1}). \quad (5)$$

Substituting (5) into (3) and (4) we find that μ_s satisfies the diffusion equation

$$\partial^2 \mu_s = \mu_s / l_{sd}^2, \quad (6)$$

where the spin diffusion length

$$l_{sd} = \sqrt{\frac{\tau_{\uparrow\downarrow}}{e^2} \frac{\sigma_\uparrow^{-1} + \sigma_\downarrow^{-1}}{N_\uparrow^{-1} + N_\downarrow^{-1}}}. \quad (7)$$

Equation (6) by means of relation (5) describes the exponential decay of non-equilibrium spin density away from a boundary.

In order to find currents $\mathbf{j}_\rho$ in each channel and the electric potential U we introduce

$$\mu_0 = \frac{\sigma_\uparrow \mu_\uparrow + \sigma_\downarrow \mu_\downarrow}{\sigma}, \quad (8)$$

where $\sigma = \sigma_\uparrow + \sigma_\downarrow$ is the net conductivity. Differentiating μ_0 yields $\mathbf{j} = \sigma \partial \mu_0 / e$, where $\mathbf{j} = \mathbf{j}_\uparrow + \mathbf{j}_\downarrow$ is the net current being conserved throughout the sample ($\partial \mathbf{j} = 0$). The spatial distribution of μ_0 is found from $\partial^2 \mu_0 = 0$, hence in one dimension

$$\mu_0(x) = \text{const} + e j x / \sigma. \quad (9)$$

The spin current $\mathbf{j}_s = \mathbf{j}_\uparrow - \mathbf{j}_\downarrow$ may then be found from the known distribution of μ_s :

$$\mathbf{j}_s = \alpha \mathbf{j} + \sigma(1 - \alpha^2) \partial \mu_s / 2e. \quad (10)$$

From the definition (2) we find that the spatial distribution of U is given by

$$-eU = \frac{N_\uparrow \mu_\uparrow + N_\downarrow \mu_\downarrow}{N_\uparrow + N_\downarrow} = \mu_0 + \frac{\beta - \alpha}{2} \mu_s, \quad (11)$$

where we have introduced the asymmetry of the density of states

$$\beta = \frac{N_\uparrow - N_\downarrow}{N_\uparrow + N_\downarrow}. \quad (12)$$

Equations (5), (6), (10), and (11) completely describe electron transport inside a layer.

At distances $\gg l_{sd}$ from boundaries, when the divergence μ_s decays to zero, the two electrochemical potentials $\mu_{\uparrow,\downarrow} = \mu_0 + \frac{1}{2}(\pm 1 - \alpha)\mu_s$ as well as the electric potential (11) collapse to μ_0 . I.e. μ_0 is the value of the electrochemical potential that would be realized were there not non-equilibrium distribution of spin. However, if measurements are done closer than l_{sd} to an interface, one has to take into account that the non-equilibrium divergence of $\mu_{\uparrow,\downarrow}$ has not yet subsided.

To find charge and current distribution through the whole multilayer sample, Eqs. (5), (6), (10), and (11) have to be supplemented by boundary conditions. In the absence of an interface resistance and spin-flip scattering, the appropriate boundary conditions are the continuity of $\mu_{\uparrow,\downarrow}$ and $\mathbf{j}_{\uparrow,\downarrow}$ [6]. The continuity of $\mu_{\uparrow,\downarrow}$ shows that μ_0 and U are discontinuous at intermetallic interfaces with the jumps

$$[\mu]_0 = \frac{1}{2}[\alpha]\mu_s, \quad -e[U] = \frac{1}{2}[\beta]\mu_s, \quad (13)$$

where $[\alpha]$ is the jump in the conduction asymmetry (1) and $[\beta]$ is the jump in the asymmetry of the density of states. The discontinuity in μ_0 appears in transport measurements farther than l_{sd} from an interface as a boundary contribution to resistances

$$R_{I\infty} = [\mu]_0 / e j = [\alpha]\mu_s / 2e j. \quad (14)$$

Discontinuities of the electrochemical potentials and the spin current may be introduced [7] to account for interface resistance and spin-flip scattering. One then has to allow for the jumps of $\mu_{\uparrow,\downarrow}$ in (13), which affects the answer (14). But the inclusion of new parameters for

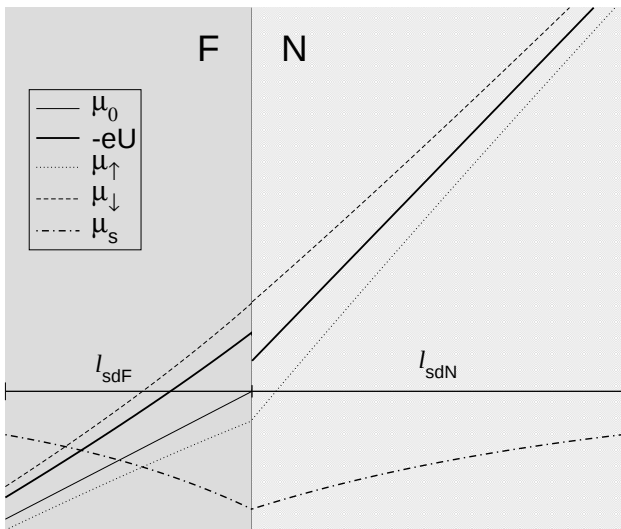


Figure 1: Sketch of spatial variation of potentials at the boundary between ferromagnetic and normal metals.

interface resistance and spin-flip scattering renders the formulas very cumbersome, not changing the principal point of the paper. Therefore, we have delegated the discussion of the interface resistance and spin-flip scattering to Appendix.

III. RESULTS

Equation (11) presents the spatial variation of the electric potential, provided μ_0 and μ_s for the problem in question are found. As revealed by its second term, if $\beta - \alpha \neq 0$, spin accumulation near an intermetallic interface causes U to collapse to its bulk asymptotic value $-\mu_0/e$ on a spin diffusion length scale. Hence, the form of the boundary contribution to resistance has to be modified dependent on how close to the boundary the measurements take place.

Anyhow, since the jump $-e[U]$ at an interface as given by the second of Eqs. (13) differs, generally speaking, from the jump of $[\mu]_0$, if measured in the immediate vicinity to the interface, instead of (14) the interface resistance would rather be

$$R_{I0} = -[U]/j = [\beta]\mu_s/2ej. \quad (15)$$

Note that the jumps $-e[U]$ and $[\mu]_0$ not only differ in absolute value, but may in principle have opposite signs.

At intermediate distances from an interface the boundary resistance must be obtained from (11): $R_{x_1x_2} = (U(x_1) - U(x_2))/j$ by a complete solution of the problem for the whole multilayer structure.

A. A Single Ferromagnetic-Nonferromagnetic Metal Interface

The solution is straightforward in the simplest case of an isolated boundary at the origin between two different materials with constants denoted by the two subscripts 1 and 2. We here have decided to illustrate our claim with more general than simply a ferromagnetic-nonferromagnetic interface example at an expense of only slightly more complex expressions.

Equating spin currents (10) we find μ_s at the origin and reestablish the Valet-Fert expression for the boundary resistance:

$$R_{I\infty} = \frac{(\alpha_1 - \alpha_2)^2}{\lambda_1 + \lambda_2}. \quad (16)$$

In this expression and below we use the shorthand notation

$$\lambda = \sigma(1 - \alpha^2)/l_{sd}. \quad (17)$$

For arbitrary $x_1 < 0$, $x_2 > 0$ the resistance between the two points is

$$R_{x_1x_2} = |x_1|/\sigma_1 + x_2/\sigma_2 + R_{I12}, \quad (18)$$

where the first two terms are the series resistances of the two materials over the lengths x_1 and x_2 respectively, and the interface contribution is

$$R_{I12} = R_{I\infty} \left(1 - \frac{(\alpha_1 - \beta_1)e^{x_1/l_{sd1}} - (\alpha_2 - \beta_2)e^{-x_2/l_{sd2}}}{\alpha_1 - \alpha_2} \right). \quad (19)$$

This expression exponentially decays from the value

$$R_{I0} = R_{I\infty} \frac{\beta_1 - \beta_2}{\alpha_1 - \alpha_2} \quad (20)$$

very close to the boundary to $R_{I\infty}$ farther than l_{sd} for it.

Note that if one of the materials is a nonferromagnetic metal, then the corresponding exponential term in (19), which describes decay of the electric potential in it, is zero. This is because in a normal metal the electric potential (11) falls onto the asymptote μ_0 right after the interface, not exponentially with the distance from it.

Position dependence of the electric potential $-eU$ and of the electrochemical potentials μ_0 , $\mu_\uparrow$, $\mu_\downarrow$, μ_s for an isolated boundary between a ferromagnetic ($\alpha_F = 0.5$, $\beta_F = -0.5$) and a normal metal ($\alpha_N = \beta_N = 0$) is plotted in Fig. 1. Note that because β_F is taken negative, the jumps $-e[U]$ and $[\mu]_0$ have opposite signs.

Allowing for interface resistance and spin-flips complicates the formulas (16), (19), and (20) without changing the qualitative conclusion of the difference between R_{I0} and $R_{I\infty}$. Expressions for boundary resistances in this case are provided in Appendix.

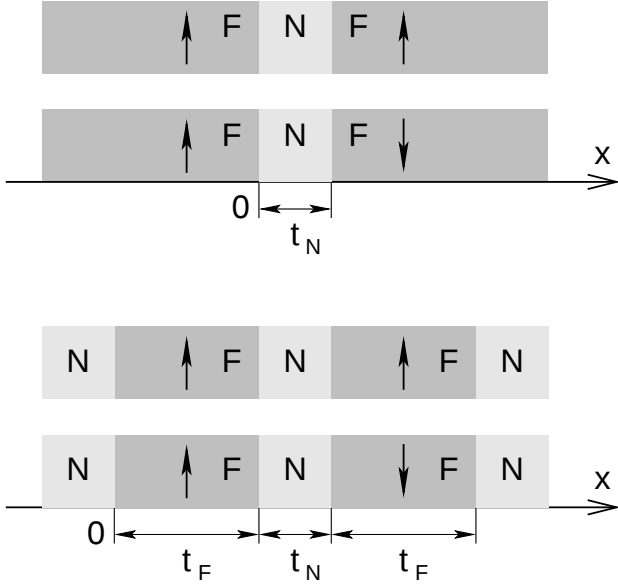


Figure 2: Sketch of a spin-valve multilayer structure, with supplying wires (two bottom structures) and without them. In each case parallel and antiparallel configurations of the two ferromagnetic layers are depicted.

B. Spin-valve Structures

In the end, we cite formulas for a simplest spin-electronic device — a trilayer ‘spin-valve’: a (thin) layer of paramagnetic metal of thickness t_N sandwiched between two ferromagnetic layers with parallel or antiparallel orientations of the magnetic momenta. We consider both the cases with and without supplying normal metal electrodes (see Fig. 2). In the first case we assume the two ferromagnetic layers to have equal thickness t_F .

In case of a symmetric trilayer without the supplying electrodes (the uppermost structure in Fig. 16) the Valet-Fert boundary resistances of the two interfaces are

$$R_{I\infty} = \frac{\alpha^2}{\lambda_F + \lambda_N \coth \theta_N / 2}, \quad (21)$$

For a symmetric five-layer with two supplying normal-metal electrodes (the third structure from the top in Fig. 2) the boundary resistances of the two external and the two internal interfaces are respectively

$$R_{Ie\infty} = \alpha^2 \frac{\lambda_N \coth \theta_N / 2 + \lambda_F \text{th} \theta_F / 2}{\lambda_F^2 + \lambda_N \lambda_F \coth \theta_F (1 + \coth \theta_N / 2) + \lambda_N^2 \coth \theta_N / 2}, \quad (27)$$

$$R_{Ii\infty} = \alpha^2 \frac{\lambda_N + \lambda_F \text{th} \theta_F / 2}{\lambda_F^2 + \lambda_N \lambda_F \coth \theta_F (1 + \coth \theta_N / 2) + \lambda_N^2 \coth \theta_N / 2}. \quad (28)$$

For an antisymmetric five-layer (the lowermost structure in Fig. 2)

$$R_{Ie\infty} = \alpha^2 \frac{\lambda_N \text{th} \theta_N / 2 + \lambda_F \text{th} \theta_F / 2}{\lambda_F^2 + \lambda_N \lambda_F \coth \theta_F (1 + \text{th} \theta_N / 2) + \lambda_N^2 \text{th} \theta_N / 2}, \quad (29)$$

$$R_{Ii\infty} = \alpha^2 \frac{\lambda_N + \lambda_F \text{th} \theta_F / 2}{\lambda_F^2 + \lambda_N \lambda_F \coth \theta_F (1 + \text{th} \theta_N / 2) + \lambda_N^2 \text{th} \theta_N / 2}. \quad (30)$$

where $\theta_N = t_N / l_{sdN}$. In the limit of large $t_N \gg l_{sdN}$ this expression turns into (16) for an isolated boundary. When the thickness of the paramagnetic layer $t_N \rightarrow 0$, we obtain that $R_{I\infty}$ vanishes as $R_{I\infty} \approx \alpha^2 t_N / 2\sigma_N$.

In what follows we omit the series contributions to resistance like the first two term in (18). For any structure in Fig. 2 these contributions are trivial. We thus simply cite the boundary part of the total resistance of a symmetric trilayer between two probe points $x_L < 0$ and $x_R > t_N$:

$$R_{IRL} = R_{I\infty} \left(2 - \frac{\alpha - \beta}{\alpha} \left(e^{x_L / l_{sdF}} + e^{(t_N - x_R) / l_{sdF}} \right) \right). \quad (22)$$

For the measurement points very close to the boundaries $x_L = 0$ and $x_R = t_N$ (22) reduces to

$$R_{I0} = 2\beta R_{I\infty} / \alpha. \quad (23)$$

For an antisymmetric trilayer without the supplying electrodes (the second structure from the top in Fig. 2), when the right ferromagnetic layer has the opposite conduction asymmetry $-\alpha$, the Valet-Fert boundary resistances are

$$R_{I\infty} = \frac{\alpha^2}{\lambda_F + \lambda_N \text{th} \theta_N / 2}. \quad (24)$$

When $t_N \rightarrow 0$ the resistance tends to a finite value $R_{I\infty} = \alpha^2 l_{sdF} / (1 - \alpha^2) \sigma_F$, thus justifying the term ‘spin-valve’. The boundary contribution to resistance between two arbitrary points $x_L < 0$ and $x_R > t_2$ is

$$R_{IRL} = R_{I\infty} \left(2 - \frac{\alpha + \beta}{\alpha} e^{(t_N - x_R) / l_{sdF}} + \frac{\alpha - \beta}{\alpha} e^{x_L / l_{sdF}} \right) \quad (25)$$

and tends to

$$R_{I0} = 2(\alpha - \beta) R_{I\infty} / \alpha \quad (26)$$

when $x_L = 0$ and $x_R = t_N$.

The boundary contribution to resistance between two arbitrary points $x_L < 0$ and $x_R > t_N + 2t_F$ is for both symmetric and antisymmetric five-layered structures simply the total boundary resistance of all the interfaces $R_{IRL} = 2(R_{I\infty} + R_{Ie\infty})$ since in the normal-metal supplying electrodes the electric potential coincides with its bulk asymptote $-\mu_0/e$ everywhere after the interface.

IV. CONCLUSIONS

In this brief study we focused on the effects of the density of states asymmetry in the diffusive transport through multilayered ferromagnetic-nonferromagnetic metal structures.

Whereas conduction asymmetry brings about spin accumulation in a layer of thickness of the order of the spin diffusion length, and determines the overall drop of the electric potential in this layer (apart from the trivial series resistance contributions), the DOS asymmetry results in a jump of the electric potential directly at an intermetallic interface. In a standard Valet-Fert theory only the boundary contributions to resistance $R_{I\infty}$ from the overall potential drop in the spin accumulation layer are calculated. These boundary resistances emerge only when measurements are done farther than the spin diffusion length from interfaces.

However, the series resistances that build up over the distance $\sim l_{sd}$ between the measurement points turn out to be larger than the boundary resistance $R_{I\infty}$. To identify the part of the resistance from the current conversion process on the boundary it is advantageous to attach probes closer to the interface. But in that case it should be remembered that because of the asymmetry of the density of states the interface contribution to the resistance differs from $R_{I\infty}$.

V. ACKNOWLEDGMENTS

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GENERAL SOLUTION OF THE EQUATIONS

In this appendix we expound the general approach we used to calculate the spatial distribution of potentials in a multilayered structure. The diffusion equation (6) in an interval $a < x < b$ in one dimension has a solution

$$\mu_s(x) = \frac{\mu_s(a) \sinh \frac{x-a}{l_{sd}} + \mu_s(b) \sinh \frac{b-x}{l_{sd}}}{\sinh \frac{b-a}{l_{sd}}} \quad (31)$$

that falls off exponentially on a length scale l_{sd} from the values $\mu_s(a)$ and $\mu_s(b)$ at the boundaries a and b .

First consider the boundaries with no interface resistance or spin-flip scattering. In this case the boundary

conditions of continuity of the electrochemical potentials and of the currents apply. The form (31) for a solution in each layer with respective l_{sd} relies on the values of μ_s on the boundaries, which thus need to be put equal on the two sides of each interface to satisfy the boundary condition of the continuity of $\mu_s = \mu_{\uparrow} - \mu_{\downarrow}$. The second boundary condition for the electrochemical potentials leads to the expression (13) for the jump of μ_0 , which together with solution (9) in each layer with respective σ yields answer for the spatial distribution (9) of μ_0 .

Substituting (31) into (10), we obtain spin currents at the boundaries:

$$\begin{aligned} j_s(a) &= \alpha j + (-B\mu_s(a) + A\mu_s(b))/2e, \\ j_s(b) &= \alpha j + (-A\mu_s(a) + B\mu_s(b))/2e, \end{aligned} \quad (32)$$

where

$$A = \frac{\lambda}{\sinh \frac{b-a}{l_{sd}}}, \quad B = \lambda \coth \frac{b-a}{l_{sd}}. \quad (33)$$

In case of a semi-infinite interval, when either $b \rightarrow \infty$ or $a \rightarrow -\infty$, μ_s on the corresponding end tends to zero and $A = 0$, $B = \lambda$.

Equating (32) on both sides of each interface, we obtain an algebraic system of equations on the interface values of μ_s . Once found, these values then give boundary resistances (14) and (15). In this way we derived Eqs. (21), (24), (27), (28), and (29), (30).

Interface resistance as well as spin-flip scattering at an interface may be taken into account by appropriate boundary conditions [7]. Non-zero surface resistance leads to discontinuity of electrochemical potential proportional to the current in the respective channel and spin-flip scattering induces discontinuity of the spin current proportional to the average value of μ_s :

$$[\mu]_{\rho} = er_{\rho}\{j\}_{\rho}, \quad [j]_s = \frac{1}{er_{sf}}\{\mu\}_s, \quad (34)$$

where $\{\dots\}$ denotes an average of a discontinuous quantity between the values on the two sides of a boundary. The surface resistances r_{ρ} in each channel may be parametrized by the total resistance $4r$ and the surface resistance asymmetry

$$\gamma = \frac{r_{\uparrow} - r_{\downarrow}}{r_{\uparrow} + r_{\downarrow}}. \quad (35)$$

Solution (31) of Eq. (6) inside a layer then obviously still holds, if $\mu_s(a)$ and $\mu_s(b)$ are understood as values of μ_s on the internal side of each boundary. Substituting this into expression (10) yields the values of the spin

current on the internal side of each boundary, which may be combined with the boundary conditions (34) to give an algebraic equation on the interface values of μ_s . However, it is easier to rewrite Eqs. (31) and (32) in terms of the average values $\{\mu\}_s$ and $\{j\}_s$ to produce:

$$\begin{aligned}\{j\}_s(a) &= \alpha_r j + (-B_r \{\mu\}_s(a) + A_r \{\mu\}_s(b))/2e, \\ \{j\}_s(b) &= \alpha_r j + (-A_r \{\mu\}_s(a) + B_r \{\mu\}_s(b))/2e\end{aligned}\quad (36)$$

in analogy with (32). Here parameters of interface resistance r , γ and of interface spin-flip scattering r_{sf} now enter only through the renormalized constants α_r , A_r , and B_r :

$$\alpha_r = \frac{\alpha - (A + B)\gamma r/2}{1 + (A + B)r/2}, \quad (37)$$

$$A_r = \frac{A(1 - r/2r_{\text{sf}})}{(1 + Br/2)^2 - (Ar/2)^2}, \quad (38)$$

$$B_r = \frac{B + (B^2 - A^2)r/2 + (1 + Br/2)/r_{\text{sf}}}{(1 + Br/2)^2 - (Ar/2)^2}. \quad (39)$$

The formal analogy between (36) and (32) allows to reuse the system of algebraic equations on the interface values of μ_s with the substitution of $\{\mu\}_s$ as variables and (37)-(39) as parameters. However, the expressions for the jumps of μ_0 and U at the boundaries are more complex than (13):

$$\begin{aligned}[\mu]_0 &= er((1 + \{\alpha\}\gamma)j + (\{\alpha\} + \gamma)\{j\}_s) + \frac{1}{2}[\alpha]\{\mu\}_s, \\ -e[U] &= er((1 + \{\beta\}\gamma)j + (\{\beta\} + \gamma)\{j\}_s) + \frac{1}{2}[\beta]\{\mu\}_s.\end{aligned}\quad (40)$$

Hence the boundary resistances (14), (15) will also be different.

As an example and to give the reader a feel of the complexity of the formulas that arise when surface resistance and spin-flips are taken into account we cite our answers for a problem considered earlier in the text with simple boundary conditions of continuity, i.e. a single boundary at the origin between two materials.

The boundary resistances farther than l_{sd} from the interface and close to it are respectively

$$R_{I\infty} = r(1 - \gamma^2) + \frac{[\alpha]^2 + r(\lambda_1(\alpha_2 + \gamma)^2 + \lambda_2(\alpha_1 + \gamma)^2) + 2r_{\text{sf}}^{-1}(\gamma + \{\alpha\})^2}{\lambda_1 + \lambda_2 + \lambda_1\lambda_2r + r_{\text{sf}}^{-1}(2 + (\lambda_1 + \lambda_2)r/2)}, \quad (42)$$

$$R_{I0} = r(1 - \gamma^2) + \frac{[\alpha][\beta] + r(\lambda_1(\alpha_2 + \gamma)(\beta_2 + \gamma) + \lambda_2(\alpha_1 + \gamma)(\beta_1 + \gamma)) + 2r_{\text{sf}}^{-1}(\gamma + \{\alpha\})(\gamma + \{\beta\})}{\lambda_1 + \lambda_2 + \lambda_1\lambda_2r + r_{\text{sf}}^{-1}(2 + (\lambda_1 + \lambda_2)r/2)}. \quad (43)$$

The dependence of the boundary resistance on the distance from the interface is given by

$$R_{I12} = R_{I\infty} + \frac{\beta_2 - \alpha_2}{2ej}\mu_s(+0)e^{-x_2/l_{\text{sd}2}} - \frac{\beta_1 - \alpha_1}{2ej}\mu_s(-0)e^{-x_1/l_{\text{sd}1}}, \quad (44)$$

where

$$\mu_s(+0) = 2ej \frac{[\alpha] + r(\lambda_1(\alpha_2 + \gamma) + (\{\alpha\} + \gamma)/4r_{\text{sf}})}{\lambda_1 + \lambda_2 + \lambda_1\lambda_2r + r_{\text{sf}}^{-1}(2 + (\lambda_1 + \lambda_2)r/2)}, \quad (45)$$

$$\mu_s(-0) = 2ej \frac{[\alpha] - r(\lambda_2(\alpha_1 + \gamma) + (\{\alpha\} + \gamma)/4r_{\text{sf}})}{\lambda_1 + \lambda_2 + \lambda_1\lambda_2r + r_{\text{sf}}^{-1}(2 + (\lambda_1 + \lambda_2)r/2)} \quad (46)$$

are the values of μ_s on the two sides of the boundary.

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